

FEATURES

- High reliability LPE GaAlAs IRLED chips
- Graded-bandgap LED structure for high radiant power output
- 880nm peak emission
- Good ohmic contacts (gold alloys)
- Good bondability

All dimensions are nominal values in inches unless otherwise specified.

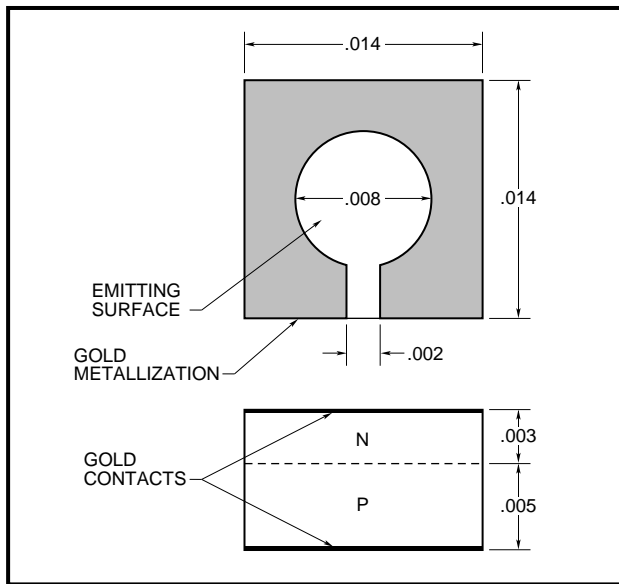
ELECTRO-OPTICAL CHARACTERISTICS AT 25°C

PARAMETERS	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Total Power Output, P _o	I _F = 100mA I _F = 20mA	8	14 2		mW
Peak Emission Wavelength, λ _p	I _F = 50mA		880		nm
Spectral Bandwidth at 50%, Δλ			80		nm
Forward Voltage, V _F	I _F = 100mA		1.55	1.9	Volts
Reverse Breakdown Voltage, V _R	I _R = 10μA	5	30		Volts
Capacitance, C	V _R = 0V		17		pF
Rise Time			0.5		μsec
Fall Time			0.5		μsec

ABSOLUTE MAXIMUM RATINGS AT 25°C

Power Dissipation	190mW
Continuous Forward Current	100mA
Peak Forward Current (10μs, 300 Hz)	3A
Reverse Voltage	5V
Storage and Operating Temperature Range	-65°C to 150°C
Maximum Junction Temperature	150°C

The exact performance data depends on your package configuration and technique. Data listed in this specification is for the chip mounted on a TO-46 header using silver epoxy as the die attach material. All sales are final after 60 days from the shipment date. Opto Diode must be notified of any discrepancies within this period.



FEATURES

- High reliability LPE GaAlAs IRLED chips
- Open center emission for imaging applications
- High output uniformity from emitting surfaces
- Gold contacts for high reliability bonding

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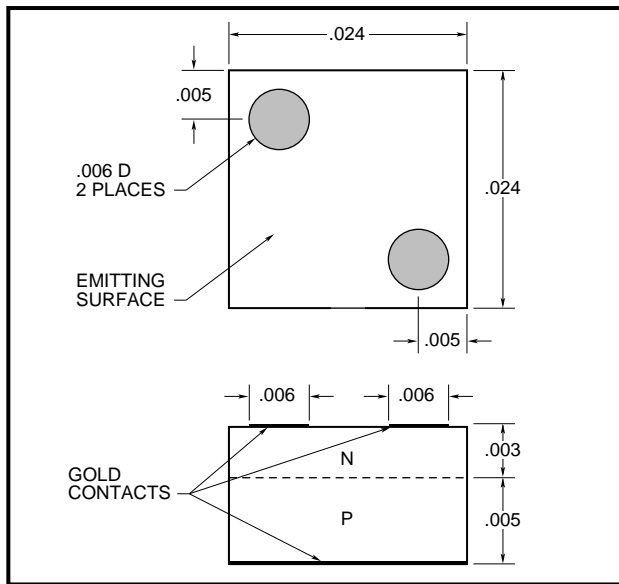
ELECTRO-OPTICAL CHARACTERISTICS AT 25°C

PARAMETERS	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Total Power Output, P_o	$I_F = 100\text{mA}$	6	8		mW
Peak Emission Wavelength, λ_p	$I_F = 50\text{mA}$		880		nm
Spectral Bandwidth at 50%, $\Delta\lambda$			80		nm
Forward Voltage, V_F	$I_F = 100\text{mA}$		1.55	1.9	Volts
Reverse Breakdown Voltage, V_R	$I_R = 10\mu\text{A}$	5	30		Volts
Capacitance, C	$V_R = 0\text{V}$		17		pF
Rise Time			0.5		μsec
Fall Time			0.5		μsec

ABSOLUTE MAXIMUM RATINGS AT 25°C

Power Dissipation	190mW
Continuous Forward Current	100mA
Peak Forward Current (10 μs , 300 Hz)	3A
Reverse Voltage	5V
Storage and Operating Temperature Range	-65°C to 150°C
Maximum Junction Temperature	150°C

The exact performance data depends on your package configuration and technique. Data listed in this specification is for the chip mounted on a TO-46 header using silver epoxy as the die attach material. All sales are final after 60 days from the shipment date. Opto Diode must be notified of any discrepancies within this period.



FEATURES

- High current capability
- 2 bond pads for uniform output
- Gold contacts for high reliability bonding
- High reliability LPE GaAlAs IRLED chips

All dimensions are nominal values in inches unless otherwise specified.

ELECTRO-OPTICAL CHARACTERISTICS AT 25°C

PARAMETERS	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Total Power Output, P_o	$I_F = 100\text{mA}$	7	10		mW
Peak Emission Wavelength, λ_p	$I_F = 50\text{mA}$		880		nm
Spectral Bandwidth at 50%, $\Delta\lambda$			80		nm
Forward Voltage, V_F	$I_F = 200\text{mA}$		1.6	2	Volts
Reverse Breakdown Voltage, V_R	$I_R = 10\mu\text{A}$	5	30		Volts
Capacitance, C	$V_R = 0\text{V}$		60		pF
Rise Time			0.7		μsec
Fall Time			0.7		μsec

ABSOLUTE MAXIMUM RATINGS AT 25°C

Power Dissipation	400mW
Continuous Forward Current	200mA
Peak Forward Current (10 μs , 300 Hz)	7A
Reverse Voltage	5V
Storage and Operating Temperature Range	-65°C to 150°C
Maximum Junction Temperature	150°C

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